(3 Hours)

Total Marks: 80

- N.B.: (1) Question number 1 is compulsory.
 - (2) Attempt any three questions from remaining questions.
 - (3) Figures to the right indicate full marks.
 - (4) Assume suitable data wherever necessary and indicate the same.
- Write a short note on following: 0.1

[20]

- Hybrid MICs versus Monolithic MICs. (a)
- Coupled Lines. (b)
- Dielectric Resonator Oscillator. (c)
- Noise correlation matrix.
- For a load impedance $Z_L = 60 i80 \Omega$, design single-stub (short circuit) shunt [10] Q.2 (a) tuning networks to match this load to a 50 \O line. Assuming that the load is matched at 2 GHz.
 - Draw and explain in detail Single-Ended Diode Mixer. (b)

[10]

- What is phase noise in oscillators? Give a mathematical analysis of phase noise. [10] Q.3

 - How is Vector Network Analyzer used to measure periodic large signal waveform [10] (b) with all harmonics.
- Design an amplifier to have a gain of 11 dB at 4.0 GHz, Plot constant-gain circle [20] Q.4 for $G_S = 2$ and 3 dB, and $G_L = 0$ and 1 dB. Calculate and plot the input return loss and overall amplifier gain from 3 to 5 GHz. The transistor has the following scattering parameters $(Z0 = 50 \Omega)$

f(GHz)	S_{22}
3 0 802-900 0 2 2 821000	0.66∠ -50°
0.75 ∠÷120° 0 2.5∠80°	0.60 ∠-70°
5 0.71∠-140° 0 2.3∠60°	0.58∠-85°

The s parameters for the HP HFET-102 FET at 2 GHZ with a bias voltage V_{gs} =0 are [10] given as follows ($Z_0=50 \Omega$)

$$S_{11} = 0.894 \angle -60.6^{\circ}$$

$$S_{21} = 3.122 \angle 123.6^{\circ}$$

$$S_{12} = 0.020 \angle 62.4^{\circ}$$

$$S_{22} = 0.781 \angle -27.6^{\circ}$$

Determine the stability of this transistor by K-delta test and plot the stability circles on smith chart.

- (b) Explain nonlinear measurements of microwave circuits with reference to load and [10] source pull.
- Q.6 (a) Show that the reflection coefficient is larger than 1 for a load of negative resistance. (10)Justify you answer using I2R relation.
 - (b) Write a short note on Field Surveys.

[10]